

IN THE SPECIFICATION

Please replace the paragraph beginning on page 7 line 13, with the following replacement paragraph:

The trench mask layer 113 is patterned to form a cell opening 115 exposing a predetermined region of the semiconductor substrate 101 at the cell region c, a high-voltage opening 116 [[115]] exposing a predetermined region of the semiconductor substrate 101 at the high-voltage region d and a key opening 117 exposing a predetermined region of the semiconductor substrate 101 at the key region e.

Please add the following paragraph *before* the paragraph beginning on page 6, line 6, *and before* the term "First Embodiment." with the following replacement paragraph:

Throughout this disclosure, the term "assistant trench" is synonymous with the term "pilot trench". In the context of this Specification, the word *assistant* and the word *pilot* convey equivalent meanings. In either case, the *assistant*, or *pilot*, trench is used as a precursor to the final trenches, as will become clear by reading through this Specification.